

ZTX951

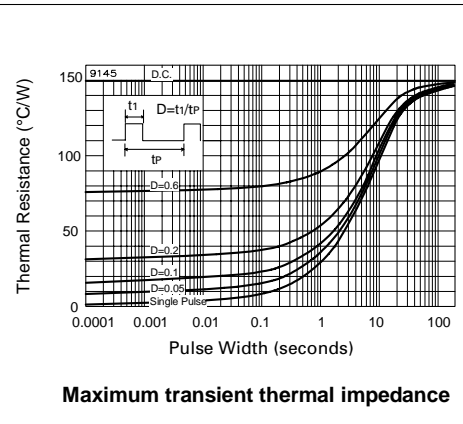
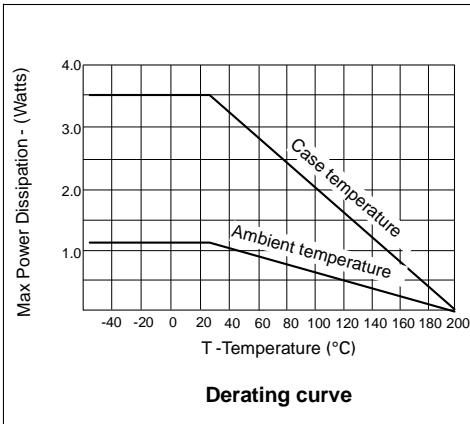
ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-850	-1000	mV	$I_C = -4\text{A}$, $V_{CE} = -1\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	100 100 75 10	200 200 120 25	300		$I_C = -10\text{mA}$, $V_{CE} = -1\text{V}^*$ $I_C = -1\text{A}$, $V_{CE} = -1\text{V}^*$ $I_C = -4\text{A}$, $V_{CE} = -1\text{V}^*$ $I_C = -10\text{A}$, $V_{CE} = -1\text{V}^*$
Transition Frequency	f_T		120		MHz	$I_C = -100\text{mA}$, $V_{CE} = -10\text{V}$ $f = 50\text{MHz}$
Output Capacitance	C_{obo}		74		pF	$V_{CB} = -10\text{V}$, $f = 1\text{MHz}$
Switching Times	t_{on} t_{off}		82 350		ns ns	$I_C = -2\text{A}$, $I_{B1} = -200\text{mA}$ $I_{B2} = -200\text{mA}$, $V_{CC} = -10\text{V}$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$

THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	MAX.	UNIT
Thermal Resistance: Junction to Ambient	$R_{th(j-amb)}$	150	$^{\circ}\text{C/W}$
Junction to Case	$R_{th(j-case)}$	50	$^{\circ}\text{C/W}$

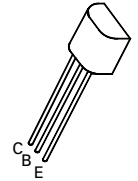


PNP SILICON PLANAR MEDIUM POWER HIGH CURRENT TRANSISTOR

ISSUE 4 – JUNE 94

ZTX951

- * 4 Amps continuous current
- * Up to 15 Amps peak current
- * Very low saturation voltage
- * Excellent gain up to 10 Amps
- * Spice model available



E-Line
TO92 Compatible

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-100	V
Collector-Emitter Voltage	V_{CEO}	-60	V
Emitter-Base Voltage	V_{EBO}	-6	V
Peak Pulse Current	I_{CM}	-15	A
Continuous Collector Current	I_C	-4	A
Practical Power Dissipation*	P_{totp}	1.58	W
Power Dissipation at $T_{amb} = 25^{\circ}\text{C}$	P_{tot}	1.2	W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +200	$^{\circ}\text{C}$

*The power which can be dissipated assuming the device is mounted in a typical manner on a P.C.B. with copper equal to 1 inch square minimum

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-100	-140		V	$I_C = -100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CER}$	-100	-140		V	$I_C = -1\mu\text{A}$, $R_B \leq 1\text{K}\Omega$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-60	-90		V	$I_C = -10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-6	-8		V	$I_E = -100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}			-50 -1	nA μA	$V_{CB} = -80\text{V}$ $V_{CB} = -80\text{V}$, $T_{amb} = 100^{\circ}\text{C}$
Collector Cut-Off Current	I_{CER} $R \leq 1\text{K}\Omega$			-50 -1	nA μA	$V_{CB} = -80\text{V}$ $V_{CB} = -80\text{V}$, $T_{amb} = 100^{\circ}\text{C}$
Emitter Cut-Off Current	I_{EBO}			-10	nA	$V_{EB} = -6\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-15 -60 -120 -220	-50 -100 -160 -300	mV mV mV mV	$I_C = -100\text{mA}$, $I_B = -10\text{mA}^*$ $I_C = -1\text{A}$, $I_B = -100\text{mA}^*$ $I_C = -2\text{A}$, $I_B = -200\text{mA}^*$ $I_C = -4\text{A}$, $I_B = -400\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-960	-1100	mV	$I_C = -4\text{A}$, $I_B = -400\text{mA}^*$

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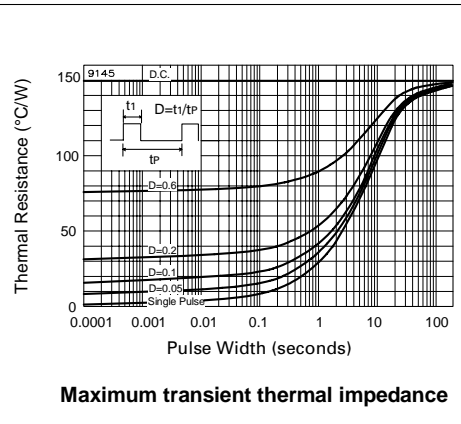
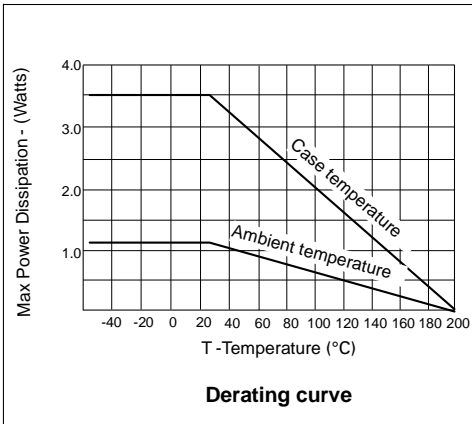
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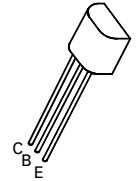


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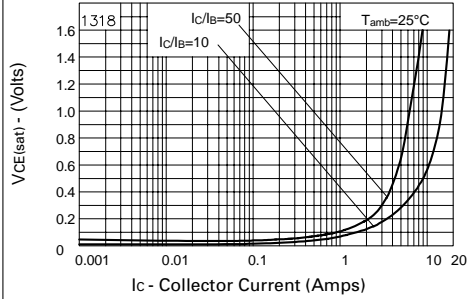
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ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

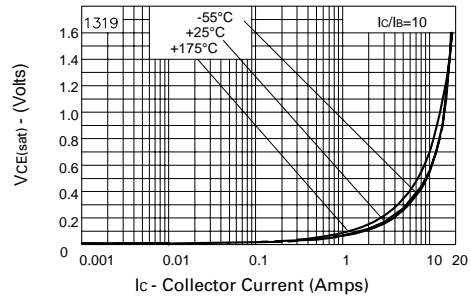
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Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-100	-140		V	$I_C = -100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CER}$	-100	-140		V	$I_C = -1\mu\text{A}$, $R_B \leq 1\text{K}\Omega$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-60	-90		V	$I_C = -10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-6	-8		V	$I_E = -100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}			-50 -1	nA μA	$V_{CB} = -80\text{V}$ $V_{CB} = -80\text{V}$, $T_{amb} = 100^{\circ}\text{C}$
Collector Cut-Off Current	I_{CER} $R \leq 1\text{K}\Omega$			-50 -1	nA μA	$V_{CB} = -80\text{V}$ $V_{CB} = -80\text{V}$, $T_{amb} = 100^{\circ}\text{C}$
Emitter Cut-Off Current	I_{EBO}			-10	nA	$V_{EB} = -6\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-15 -60 -120 -220	-50 -100 -160 -300	mV mV mV mV	$I_C = -100\text{mA}$, $I_B = -10\text{mA}^*$ $I_C = -1\text{A}$, $I_B = -100\text{mA}^*$ $I_C = -2\text{A}$, $I_B = -200\text{mA}^*$ $I_C = -4\text{A}$, $I_B = -400\text{mA}^*$
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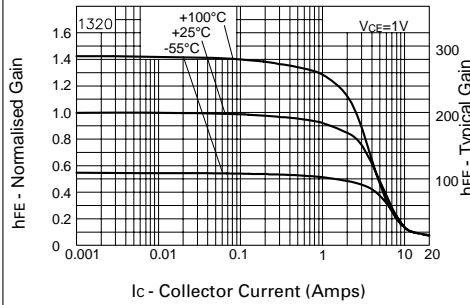
TYPICAL CHARACTERISTICS



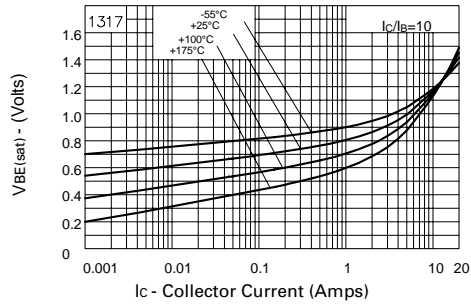
$V_{CE(sat)}$ v I_C



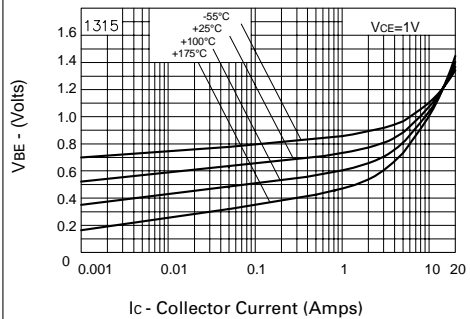
$V_{CE(sat)}$ v I_C



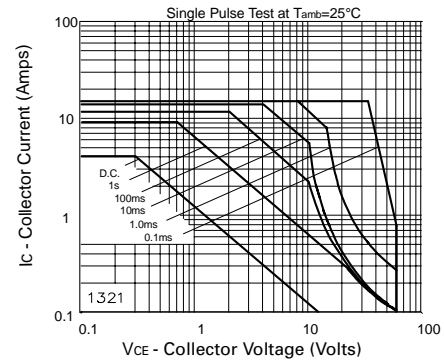
h_{FE} v I_C



$V_{BE(sat)}$ v I_C



$V_{BE(on)}$ v I_C



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